

**40V N-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
40V	34mΩ @ $V_{GS} = 10V$	7.2A
	59mΩ @ $V_{GS} = 4.5V$	5.5A

**Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- Max  $Q_g$  rated
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

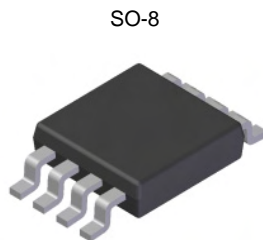
**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

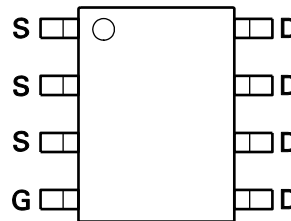
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

**Mechanical Data**

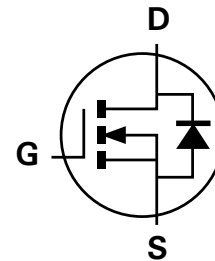
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)



Top View



Top View



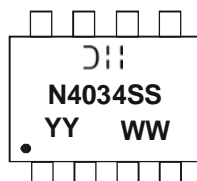
Equivalent Circuit

**Ordering Information** (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN4034SSS-13	N4034SS	13	12	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

**Marking Information**



DII = Manufacturer's Marking  
 N4034SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01 - 53)

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

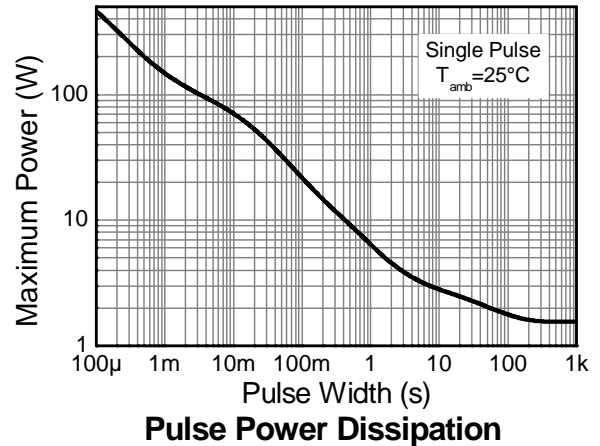
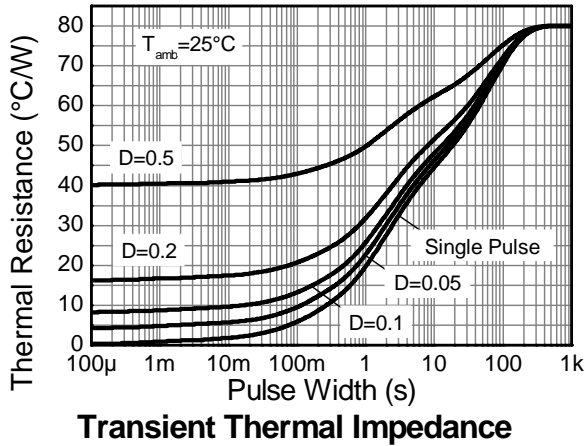
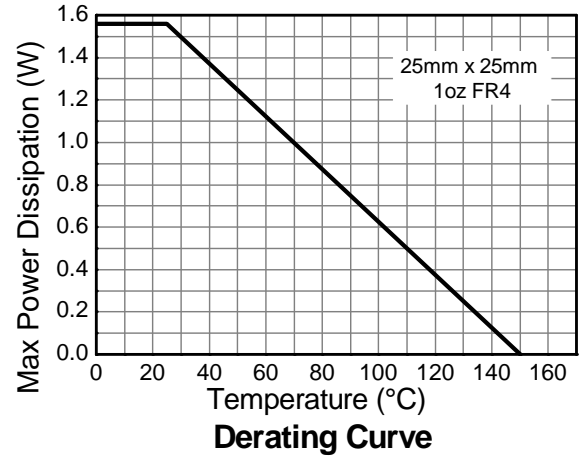
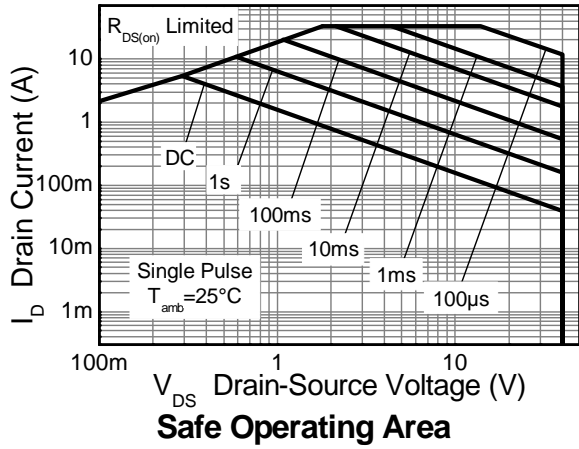
Characteristic		Symbol	Value	Unit
Drain-Source voltage		$V_{DSS}$	40	V
Gate-Source voltage	(Note 2)	$V_{GS}$	$\pm 20$	V
Single Pulsed Avalanche Energy		(Note 7)	$E_{AS}$	27
Single Pulsed Avalanche Current		(Note 7)	$I_{AS}$	15.25
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 4)	$I_D$	7.2
		$T_A = 70^\circ\text{C}$ (Note 4)		5.8
		(Note 3)		5.4
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 5)	$I_{DM}$	33.0
Continuous Source current (Body diode)		(Note 4)	$I_S$	4.1
Pulsed Source current (Body diode)		(Note 5)	$I_{SM}$	33.0

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 3)	$P_D$	1.56	W
	Linear derating factor		12.5	
(Note 4)			2.8	
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JA}$	80	$^\circ\text{C/W}$
	(Note 4)		44.5	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	37	
Operating and storage temperature range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

- Notes:
- AEC-Q101  $V_{GS}$  maximum is  $\pm 16\text{V}$ .
  - For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as note (3), except the device is measured at  $t \leq 10$  sec.
  - Same as note (3), except the device is pulsed with  $D = 0.02$  and pulse width 300 $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
  - Thermal resistance from junction to solder-point (at the end of the drain lead).
  - UIS in production with  $L = 100\mu\text{H}$ ,  $V_{DD} = 40\text{V}$ .

**Thermal Characteristics**

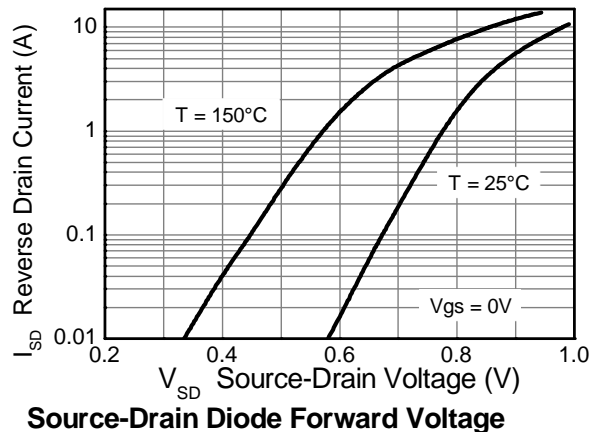
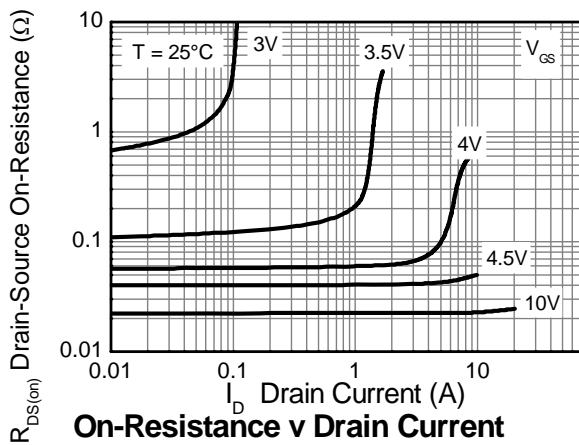
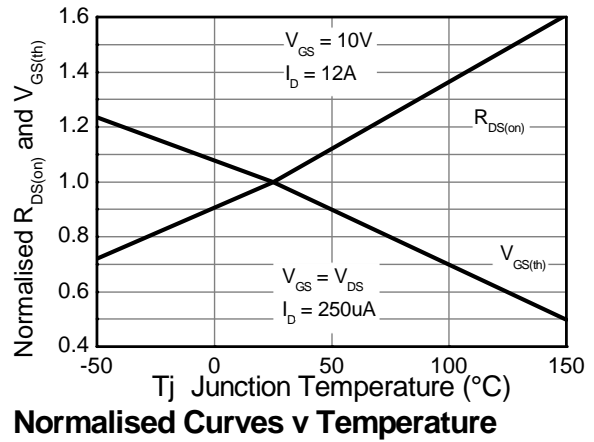
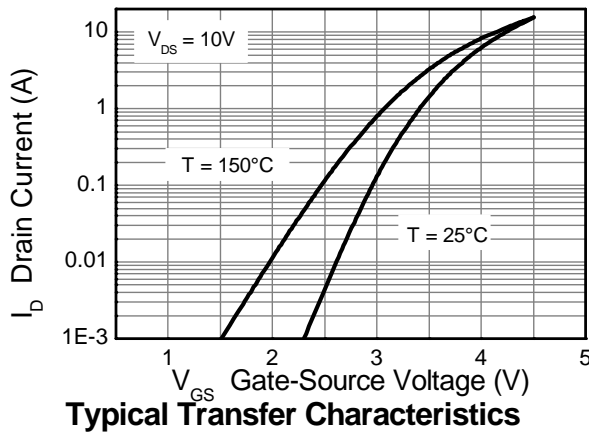
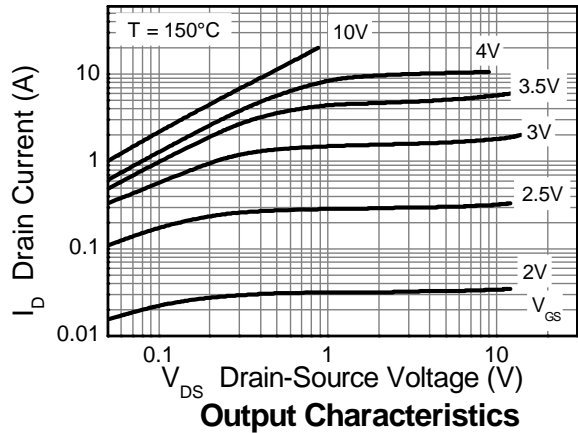
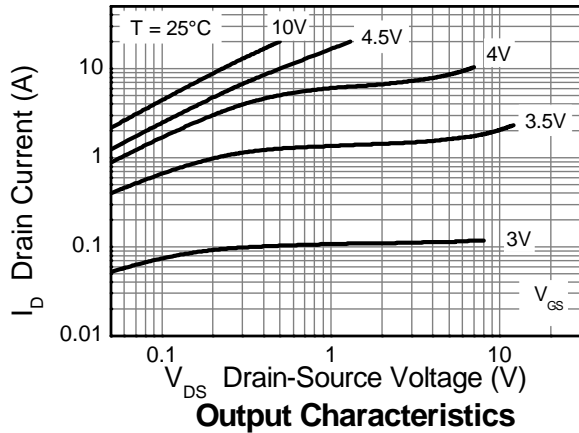


**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

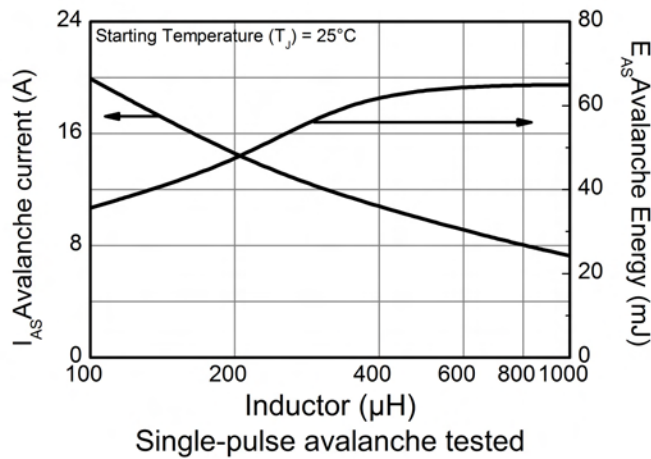
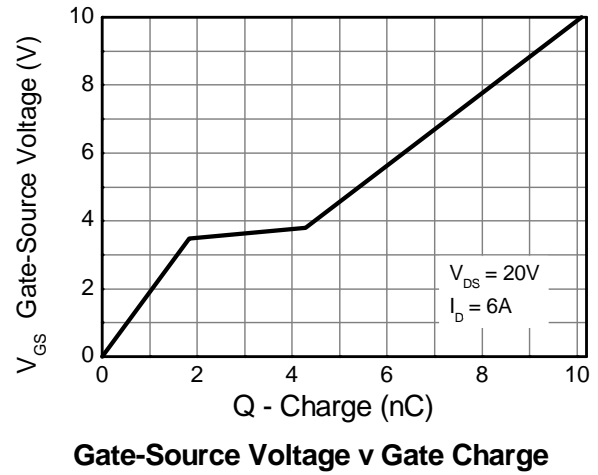
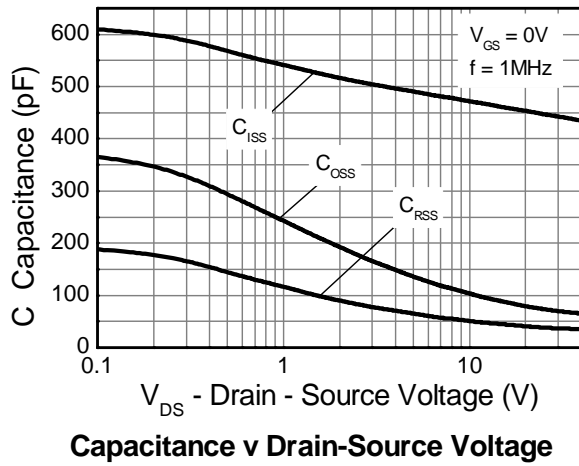
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	3.0	V	I <sub>D</sub> = 250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(on)</sub>	—	0.023	0.034	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A
			0.039	0.059		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A
Forward Transconductance (Notes 8 & 9)	g <sub>fs</sub>	—	20.5	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 6A
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	—	0.87	1.1	V	I <sub>S</sub> = 6A, V <sub>GS</sub> = 0V
Reverse recovery time (Note 9)	t <sub>rr</sub>	—	11.9	—	ns	I <sub>S</sub> = 2.5A, di/dt = 100A/μs
Reverse recovery charge (Note 9)	Q <sub>rr</sub>	—	4.9	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	453	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	79.1	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	40.5	—	pF	
Total Gate Charge (Note 10)	Q <sub>g</sub>	—	4.9	8	nC	V <sub>GS</sub> = 4.5V
Total Gate Charge (Note 10)	Q <sub>g</sub>	—	10	18	nC	V <sub>GS</sub> = 10V
Gate-Source Charge (Note 10)	Q <sub>gs</sub>	—	1.8	—	nC	
Gate-Drain Charge (Note 10)	Q <sub>gd</sub>	—	2.4	—	nC	
Turn-On Delay Time (Note 10)	t <sub>D(on)</sub>	—	2.7	—	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V I <sub>D</sub> = 1A, R <sub>G</sub> ≅ 6.0Ω
Turn-On Rise Time (Note 10)	t <sub>r</sub>	—	2.7	—	ns	
Turn-Off Delay Time (Note 10)	t <sub>D(off)</sub>	—	14	—	ns	
Turn-Off Fall Time (Note 10)	t <sub>f</sub>	—	6	—	ns	

- Notes:
- 8. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
  - 9. For design aid only, not subject to production testing.
  - 10. Switching characteristics are independent of operating junction temperatures.

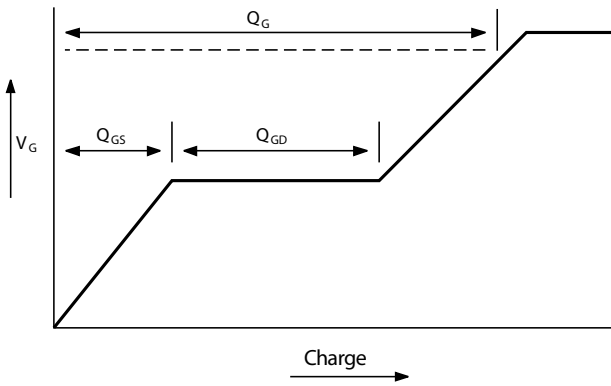
**Typical Characteristics**



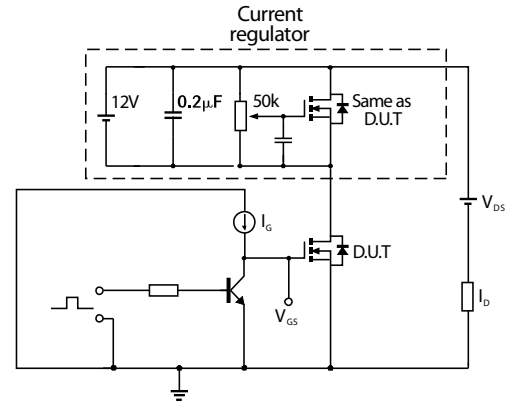
**Typical Characteristics – continued**



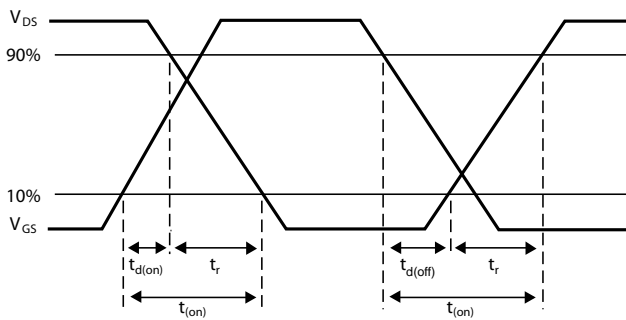
**Test Circuits**



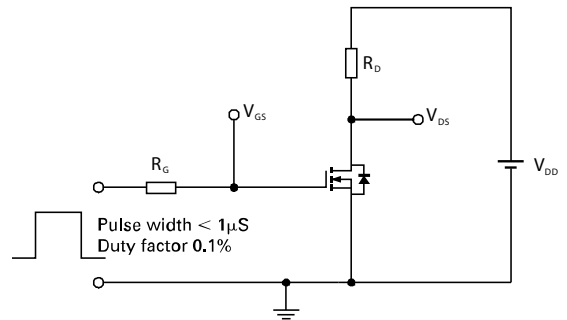
**Basic gate charge waveform**



**Gate charge test circuit**

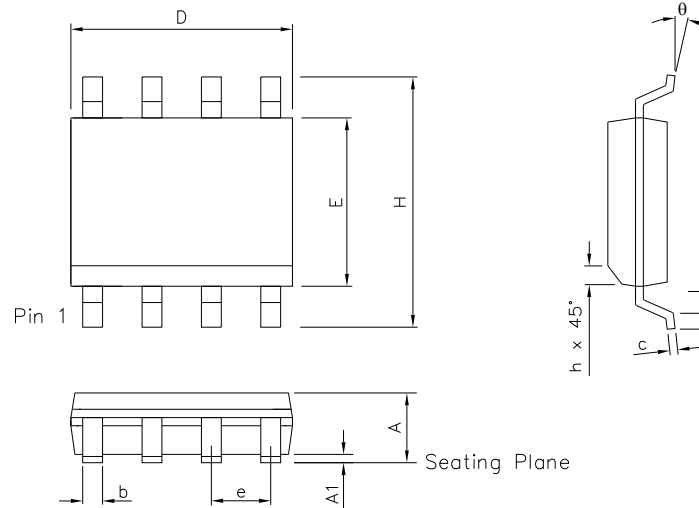


**Switching time waveforms**



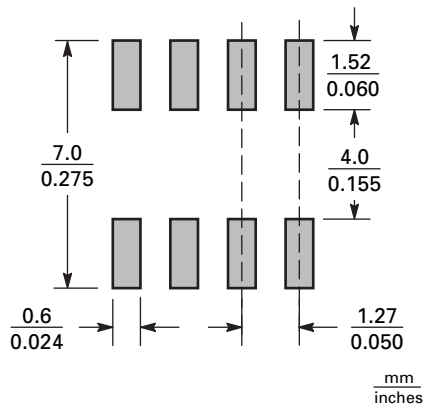
**Switching time test circuit**

**Package Outline Dimensions**



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	theta	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

**Suggested Pad Layout**



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